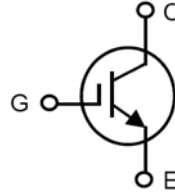


**1200V XPT™  
GenX4™ IGBT**
**IXYA30N120A4HV  
IXYP30N120A4  
IXYH30N120A4**

 Ultra Low-V<sub>sat</sub> PT IGBT for  
up to 5kHz Switching


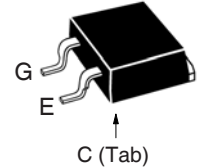
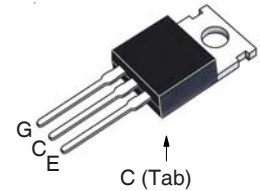
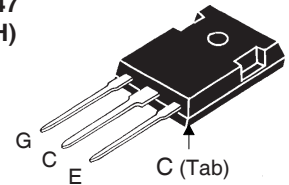
$$V_{CES} = 1200V$$

$$I_{C110} = 30A$$

$$V_{CE(sat)} \leq 1.9V$$

$$t_{fi(typ)} = 147ns$$

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $175^\circ C$	1200	V
$V_{CGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GE} = 1M\Omega$	1200	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	106	A
$I_{C110}$	$T_C = 110^\circ C$	30	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	184	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 5\Omega$ Clamped Inductive Load	$I_{CM} = 60$ $V_{CE} \leq 0.8 \cdot V_{CES}$	A
$P_C$	$T_C = 25^\circ C$	500	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$F_C$	Mounting Force (TO-263HV)	10..65 / 2.2..14.6	N/lb
$M_d$	Mounting Torque (TO-220 & TO-247)	1.13 / 10	Nm/lb.in
<b>Weight</b>	TO-263HV	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

**TO-263HV**  
(IXYA..HV)

**TO-220**  
(IXYP)

**TO-247**  
(IXYH)

 G = Gate      C = Collector  
 E = Emitter    Tab = Collector

**Features**

- Optimized for Low Conduction
- Positive Thermal Coefficient of V<sub>ce(sat)</sub>
- International Standard Packages

**Advantages**

- High Power Density
- Low Gate Drive Requirement

**Applications**

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	4.0		6.5 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 150^\circ C$			10 $\mu A$ 500 $\mu A$
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 25A$ , $V_{GE} = 15V$ , Note 1 $T_J = 150^\circ C$		1.6 1.9	V V

Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 25\text{A}, V_{CE} = 10\text{V}$ , Note 1	10	16	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		1150	pF
$C_{oes}$			70	pF
$C_{res}$			40	pF
$Q_{g(on)}$	$I_C = 25\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		57	nC
$Q_{ge}$			8	nC
$Q_{gc}$			26	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 25\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.8 \cdot V_{CES}, R_G = 5\Omega$ Note 2		15	ns
$t_{ri}$			42	ns
$E_{on}$			4.0	mJ
$t_{d(off)}$			235	ns
$t_{fi}$			147	ns
$E_{off}$			3.4	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 25\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.8 \cdot V_{CES}, R_G = 5\Omega$ Note 2		13	ns
$t_{ri}$			33	ns
$E_{on}$			4.8	mJ
$t_{d(off)}$			316	ns
$t_{fi}$			270	ns
$E_{off}$			5.6	mJ
$R_{thJC}$	TO-220 TO-247			0.30 $^\circ\text{C/W}$
$R_{thCS}$			0.50 0.21	$^\circ\text{C/W}$ $^\circ\text{C/W}$

**Notes:**

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}$  (clamp),  $T_J$  or  $R_G$ .

**ADVANCE TECHNICAL INFORMATION**

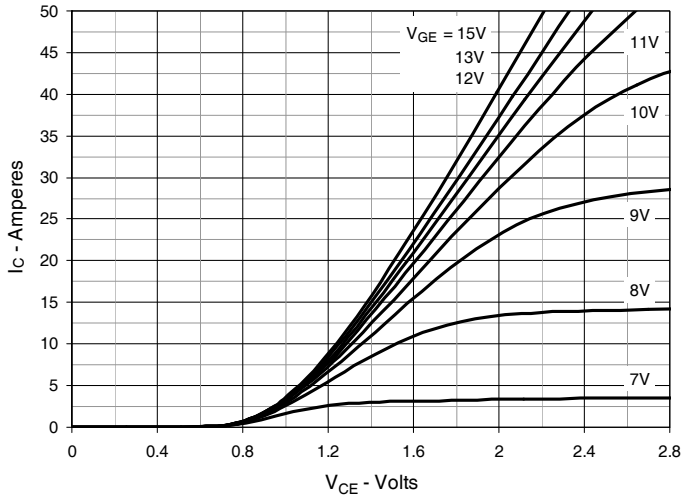
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

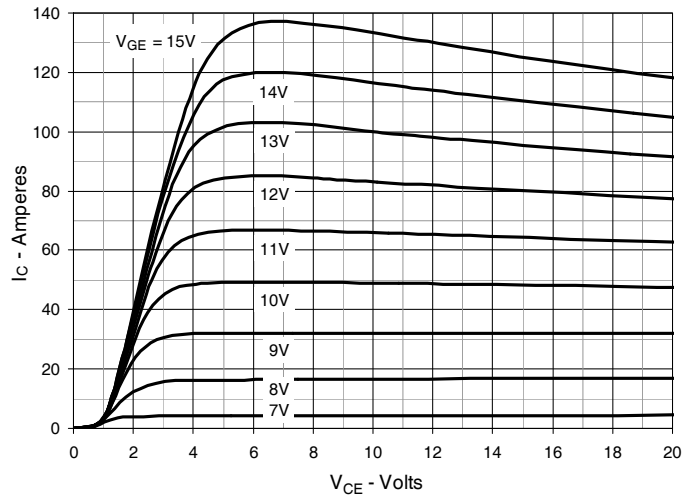
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

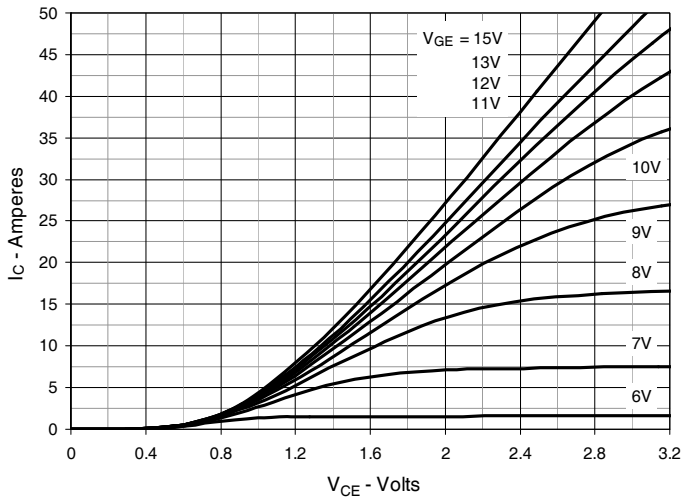
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



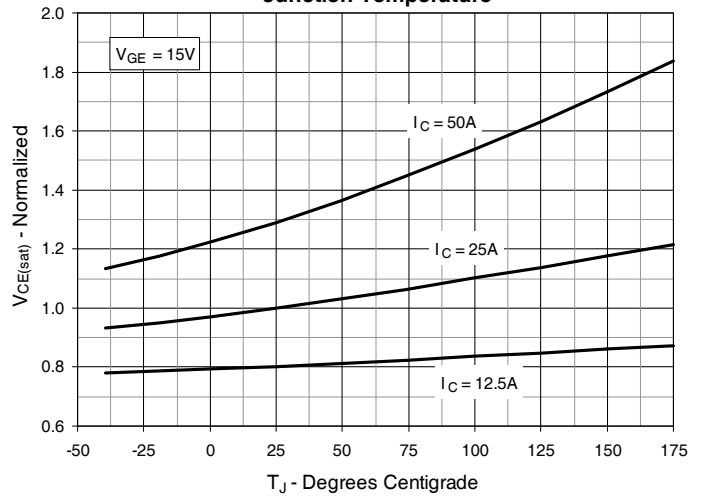
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



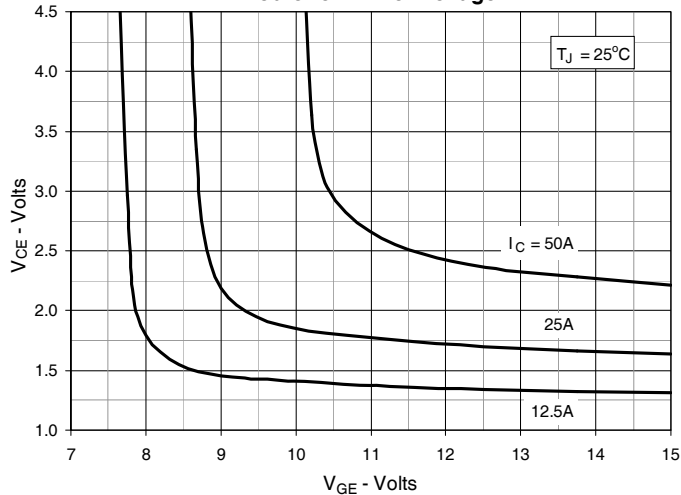
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



**Fig. 6. Input Admittance**

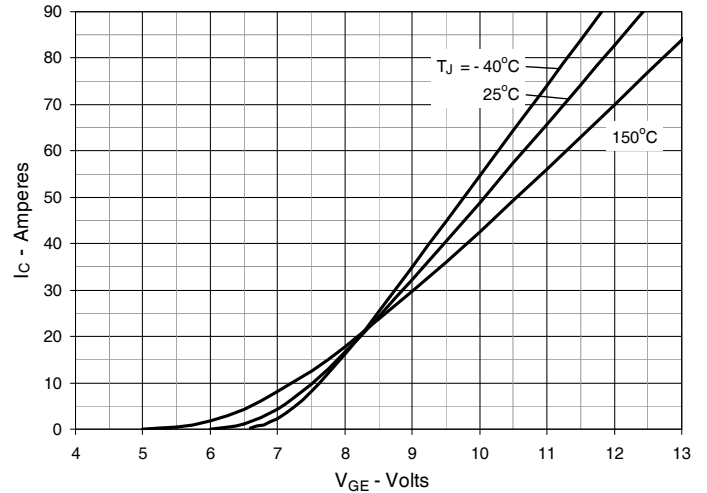


Fig. 7. Transconductance

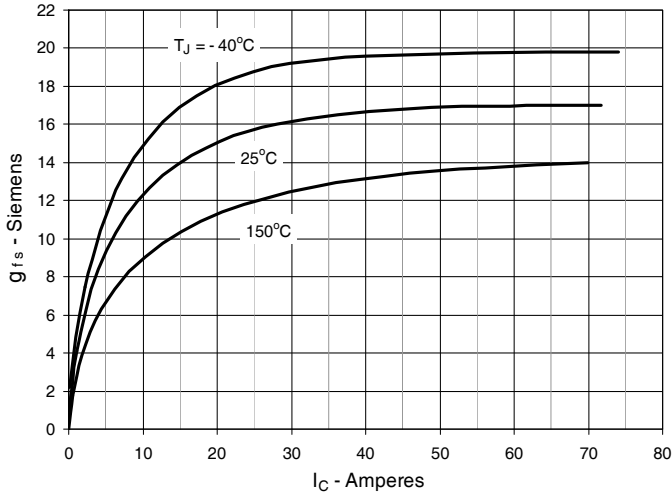


Fig. 8. Gate Charge

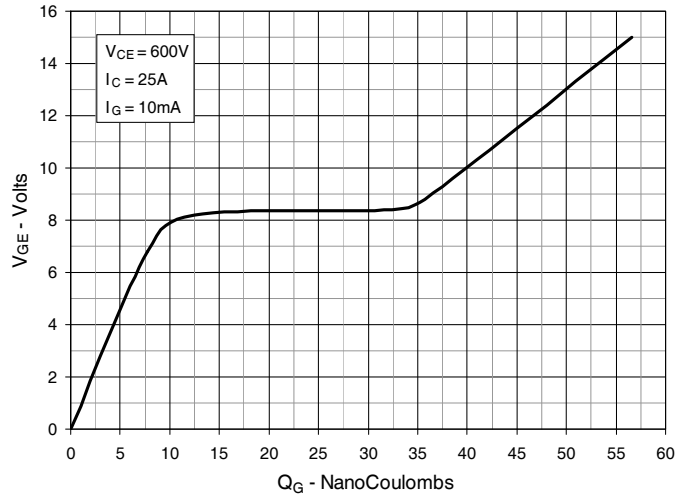


Fig. 9. Capacitance

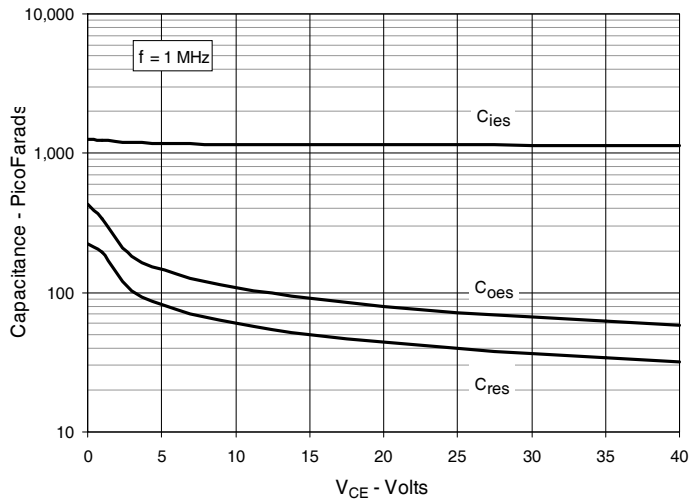


Fig. 10. Reverse-Bias Safe Operating Area

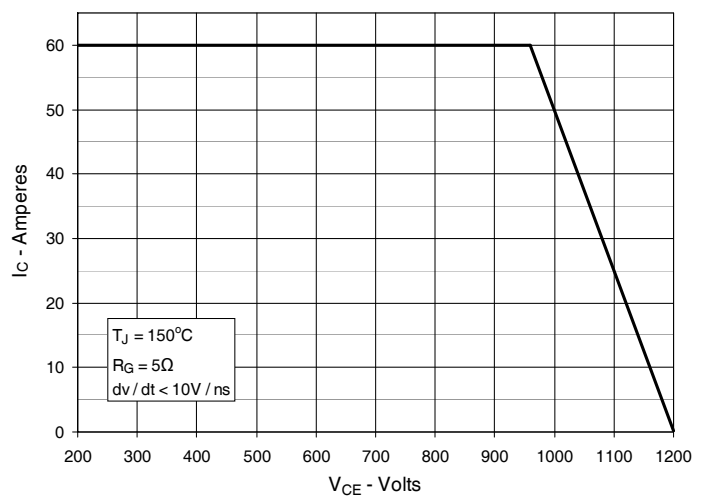
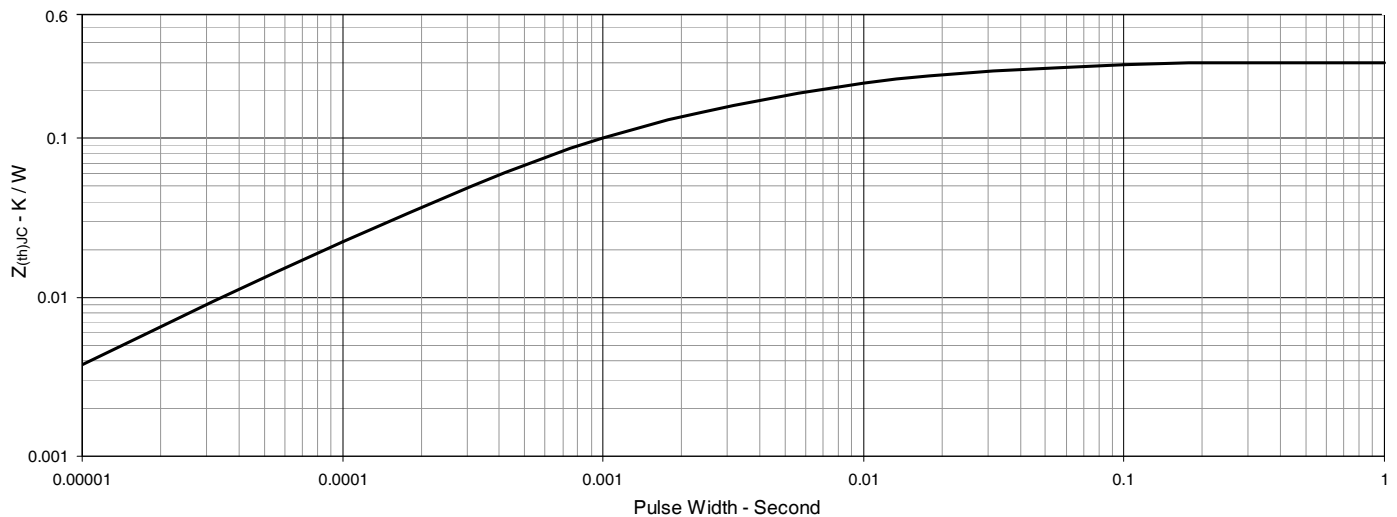
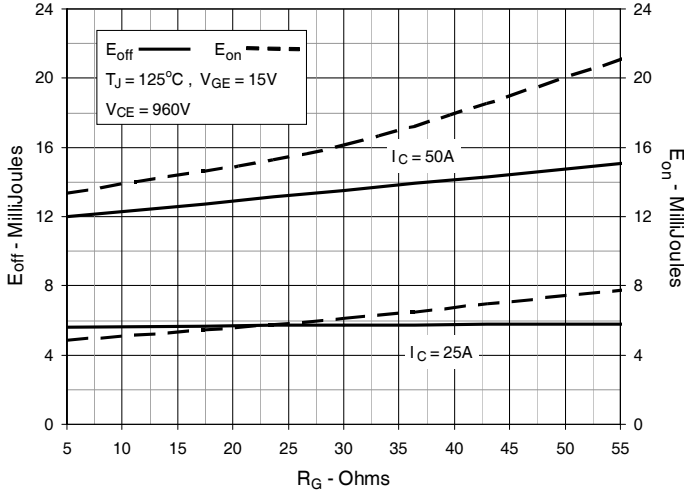


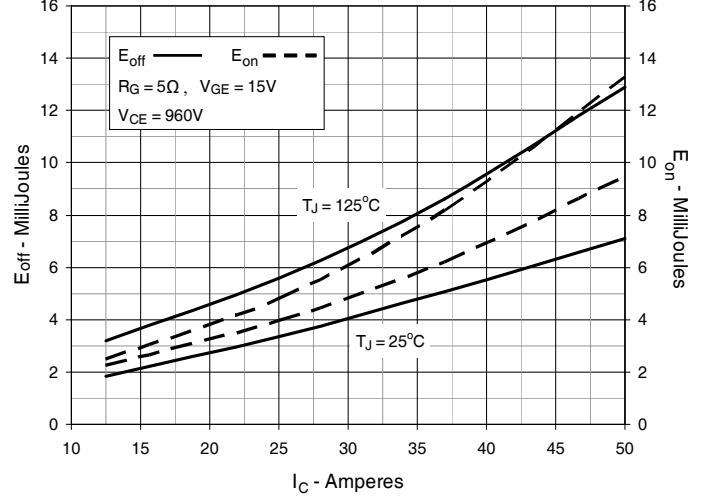
Fig. 11. Maximum Transient Thermal Impedance



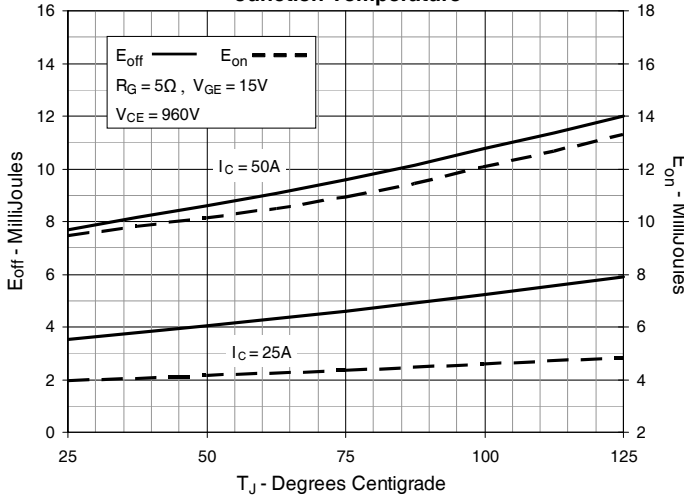
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



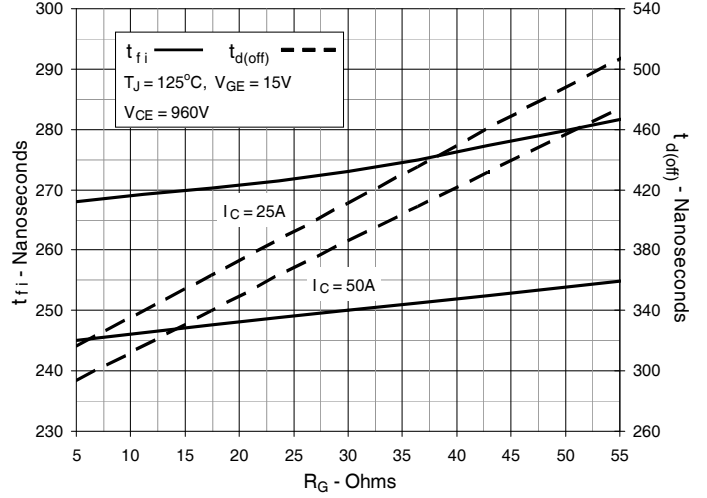
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



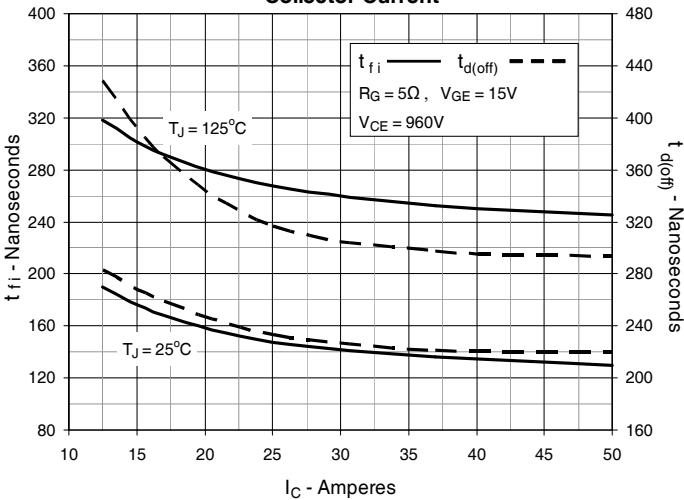
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



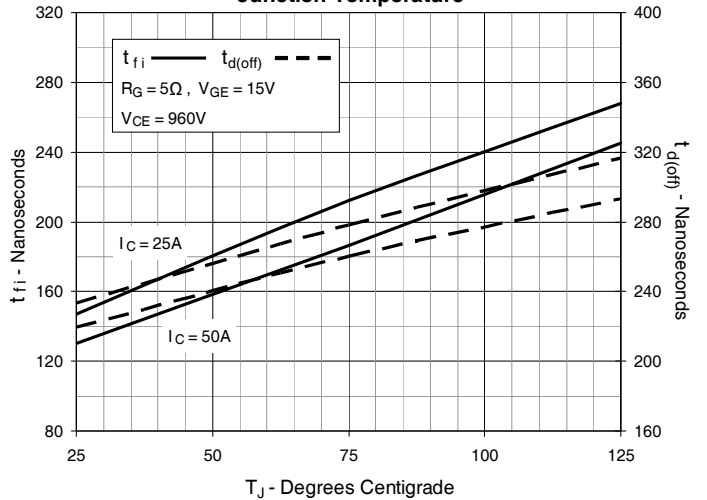
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



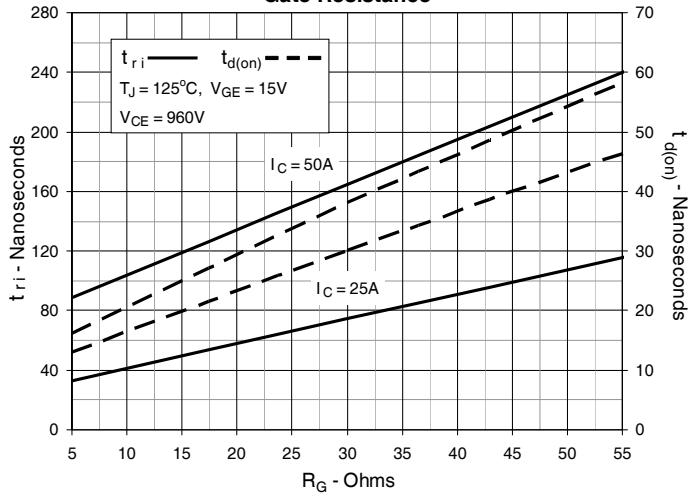
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



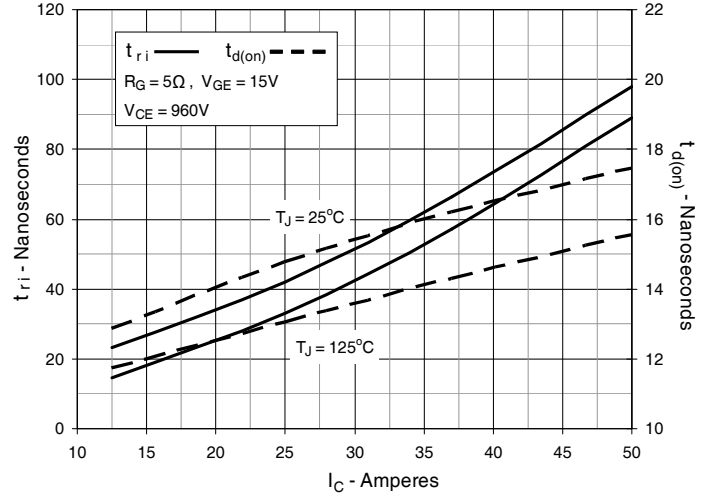
**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**



**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**

